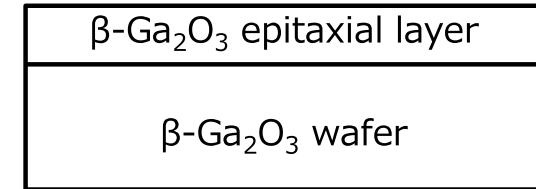


Standard specifications of 100 mm β -Ga₂O₃ epitaxial wafer (by HVPE)

Epitaxial layer

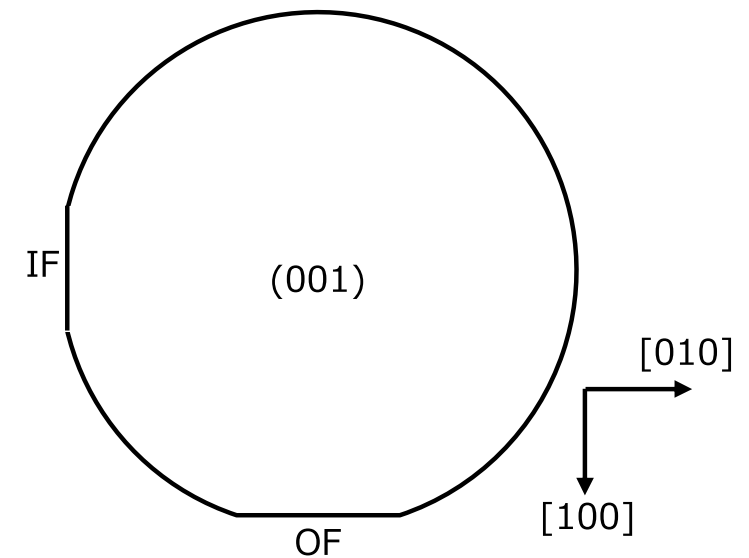
Items	Specifications
Dopant	Si (n-type)
Doping concentration	Specify a value in the range between 2×10^{16} and $9 \times 10^{16} \text{ cm}^{-3}$
Thickness	Specify a value in the range between 5 and 10 μm



Cross section of β -Ga₂O₃ epitaxial wafer

Wafer

Items	Specifications
Dopant	Sn (n-type)
Doping concentration	$1 \times 10^{18} \sim 2 \times 10^{19} \text{ cm}^{-3}$
Orientation	(001)
Size	100 mm
Thickness	0.65 mm
XRD FWHM	$\leq 350 \text{ arcsec}$
Off set angle	$0^\circ \pm 1^\circ$



Orientation



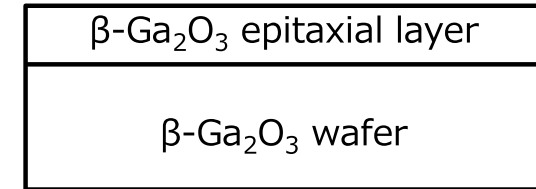
Remarks

- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.

Standard specifications of 2 inch β -Ga₂O₃ epitaxial wafer (by HVPE)

Epitaxial layer

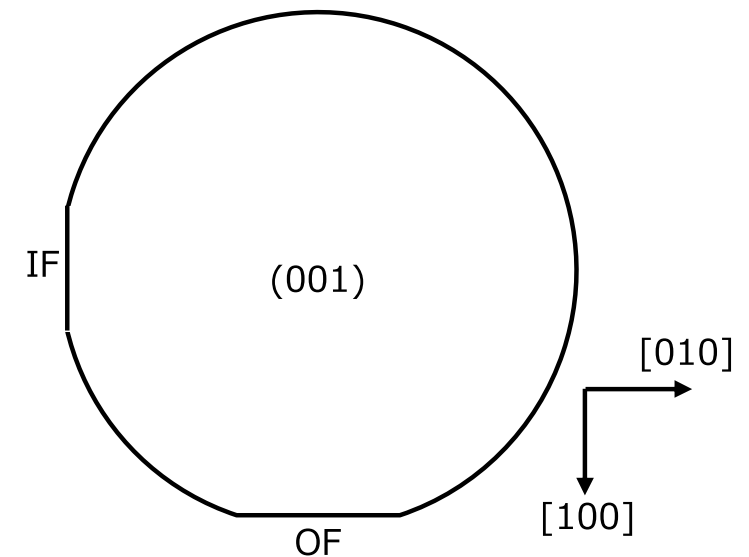
Items	Specifications
Dopant	Si (n-type)
Doping concentration	Specify a value in the range between 1×10^{16} and $9 \times 10^{16} \text{ cm}^{-3}$
Thickness	Specify a value in the range between 5 and 10 μm



Cross section of β -Ga₂O₃ epitaxial wafer

Wafer

Items	Specifications
Dopant	Sn (n-type)
Doping concentration	$1 \times 10^{18} \sim 2 \times 10^{19} \text{ cm}^{-3}$
Orientation	(001)
Size	2 inch
Thickness	0.65 mm
XRD FWHM	$\leq 350 \text{ arcsec}$
Off set angle	$0^\circ \pm 1^\circ$



Orientation



Remarks

- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.